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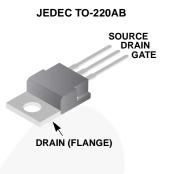
HUF75542P3

Data Sheet

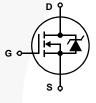
October 2013

N-Channel UltraFET Power MOSFET 80 V, 75 A, 14 mΩ

Packaging



Symbol



Features

- Ultra Low On-Resistance
 - $r_{DS(ON)} = 0.014\Omega, V_{GS} = 10V$
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Electrical Models
 - Spice and SABER Thermal Impedance Models
 - www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve

Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75542P3	TO-220AB	75542P

7554000

Absolute Maximum Ratings	$T_{C} = 25^{\circ}C$, Unless Otherwise Specified
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	HUF75542P3	UNITS
Drain to Source Voltage (Note 1)	80	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)V _{DGR}	80	V
Gate to Source Voltage	±20	V
$ \begin{array}{c} \text{Drain Current} \\ \text{Continuous } (T_C = 25^{\circ}\text{C}, V_{GS} = 10\text{V}) \text{ (Figure 2)} \\ \text{Continuous } (T_C = 100^{\circ}\text{C}, V_{GS} = 10\text{V}) \text{ (Figure 2)} \\ \text{Pulsed Drain Current} \\ \text{Pulsed Avalanche Rating} \\ \end{array} $	75 58 Figure 4 Figures 6, 14, 15	A A
Power Dissipation	230 1.54	W W/ ^o C
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10sT _L Package Body for 10s, See Techbrief TB334T _{pkg} NOTE:	300 260	°C ℃

1. $T_J = 25^{\circ}C$ to $150^{\circ}C$.

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Product reliability information can be found at http://www.fairchildsemi.com/products/discrete/reliability/index.html For severe environments, see our Automotive HUFA series.

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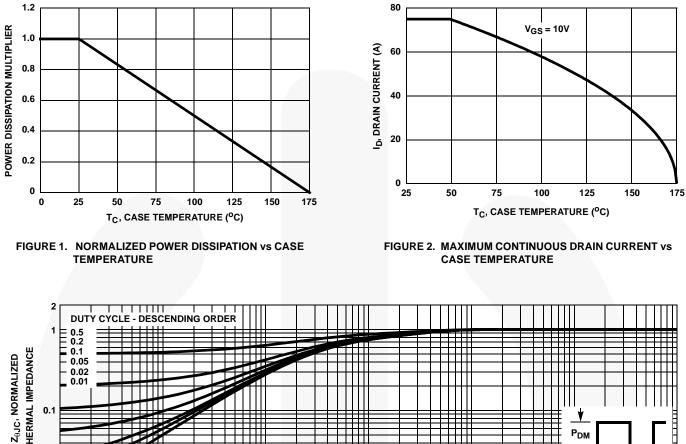
PARAMETER	SYMBOL	TEST CONDITIONS		MIN	ТҮР	МАХ	UNITS
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV _{DSS}	$I_D = 250\mu A, V_{GS} = 0V$ (Figure 11)		80	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 75V, V_{GS} = 0^{10}$	V	-	-	1	μΑ
		$V_{\rm DS} = 70V, V_{\rm GS} = 0^{10}$	V, T _C = 150 ^o C	-	-	250	μA
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20V$		-	-	±100	nA
ON STATE SPECIFICATIONS	1						
Gate to Source Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{D} = 250$	μA (Figure 10)	2	-	4	V
Drain to Source On Resistance	r _{DS(ON)}	I _D = 75A, V _{GS} = 10V	(Figure 9)	-	0.012	0.014	Ω
THERMAL SPECIFICATIONS						I	1
Thermal Resistance Junction to Case	R _{θJC}	TO-220		-	-	0.65	°C/W
Thermal Resistance Junction to Ambient	R _{θJA}			-	-	62	°C/W
SWITCHING SPECIFICATIONS (V_{GS}	= 10V)			I			1
Turn-On Time	ton	$V_{DD} = 40V, I_D = 75A$ $V_{GS} = 10V,$ $R_{GS} = 3.9\Omega$ (Figures 18, 19)		-	-	195	ns
Turn-On Delay Time	t _{d(ON)}			-	12.5	-	ns
Rise Time	t _r			-	117	-	ns
Turn-Off Delay Time	t _{d(OFF)}			-	50	-	ns
Fall Time	t _f			-	80	-	ns
Turn-Off Time	^t OFF			-	-	195	ns
GATE CHARGE SPECIFICATIONS	1						1
Total Gate Charge	Q _{g(TOT)}	$V_{GS} = 0V$ to 20V	$V_{DD} = 40V,$	-	150	180	nC
Gate Charge at 10V	Q _{g(10)}	$V_{GS} = 0V \text{ to } 10V$	[─] I _D = 75A, I _{g(REF)} = 1.0mA	-	80	96	nC
Threshold Gate Charge	Q _{g(TH)}	$V_{GS} = 0V \text{ to } 2V$	(Figures 13, 16, 17)	-	5.7	7	nC
Gate to Source Gate Charge	Q _{gs}	-		-	15	-	nC
Gate to Drain "Miller" Charge	Q _{gd}			-	33	-	nC
CAPACITANCE SPECIFICATIONS		1		1		1	1
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 12)		-	2750	-	pF
Output Capacitance	C _{OSS}			-	700	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	250	-	pF

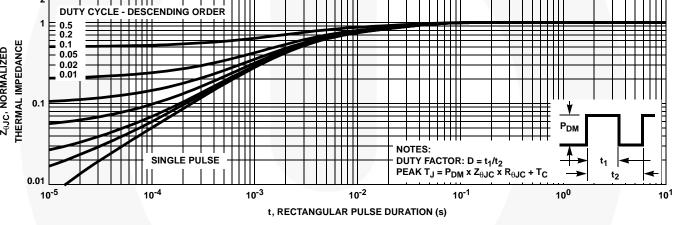
Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V _{SD}	I _{SD} = 75A	-	-	1.25	V
		I _{SD} = 37.5A	-	-	1.00	V
Reverse Recovery Time	t _{rr}	I _{SD} = 75A, dI _{SD} /dt = 100A/μs	-	-	102	ns
Reverse Recovered Charge	Q _{RR}	I _{SD} = 75A, dI _{SD} /dt = 100A/μs	-	-	255	nC

Typical Performance Curves







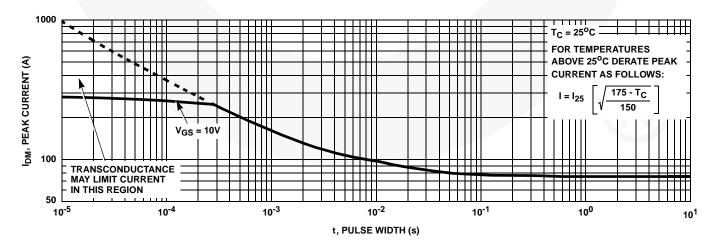


FIGURE 4. PEAK CURRENT CAPABILITY

Typical Performance Curves (Continued)

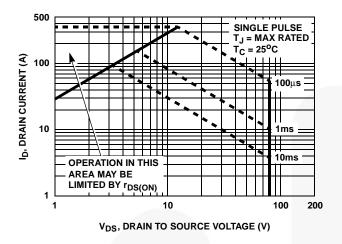


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA

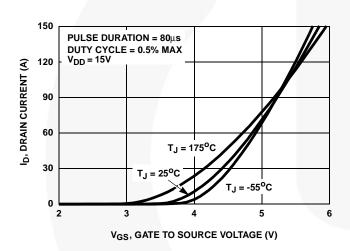
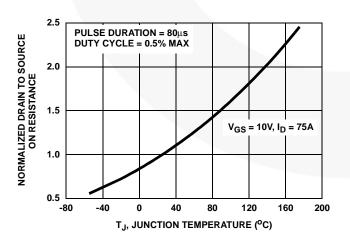
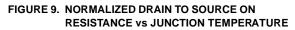
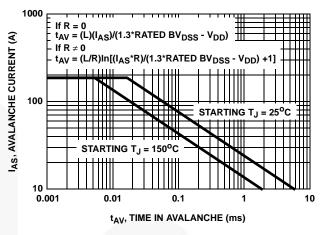


FIGURE 7. TRANSFER CHARACTERISTICS

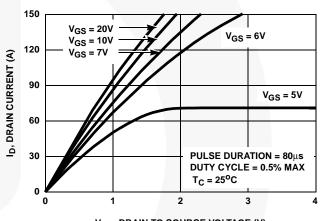






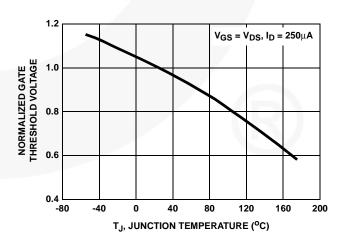
NOTE: Refer to Fairchild Application Notes AN9321 and AN9322. FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

CAPABILITY



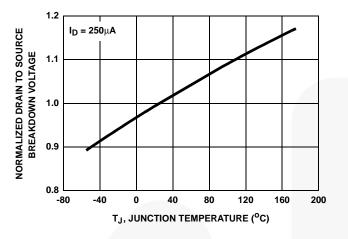
V_{DS}, DRAIN TO SOURCE VOLTAGE (V)

FIGURE 8. SATURATION CHARACTERISTICS





Typical Performance Curves (Continued)





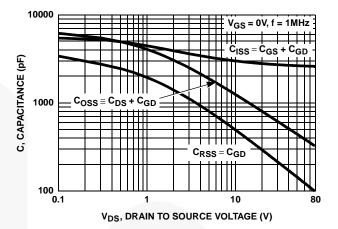
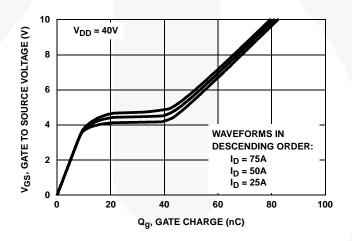
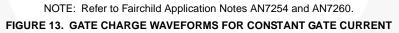


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE





Test Circuits and Waveforms

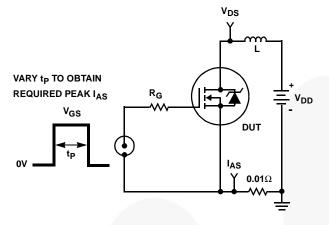


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

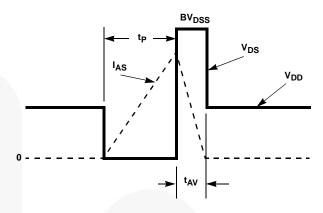


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

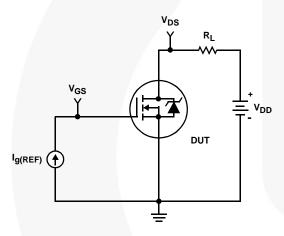


FIGURE 16. GATE CHARGE TEST CIRCUIT

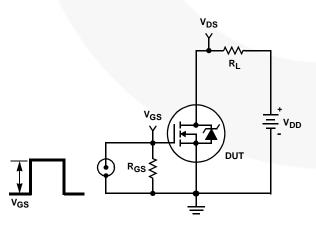
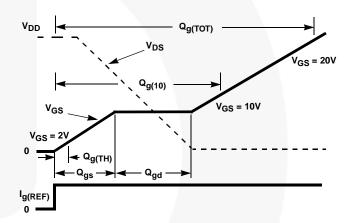


FIGURE 18. SWITCHING TIME TEST CIRCUIT





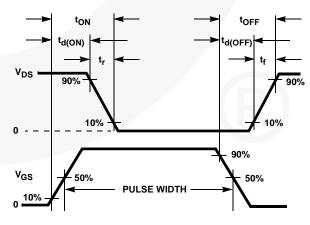
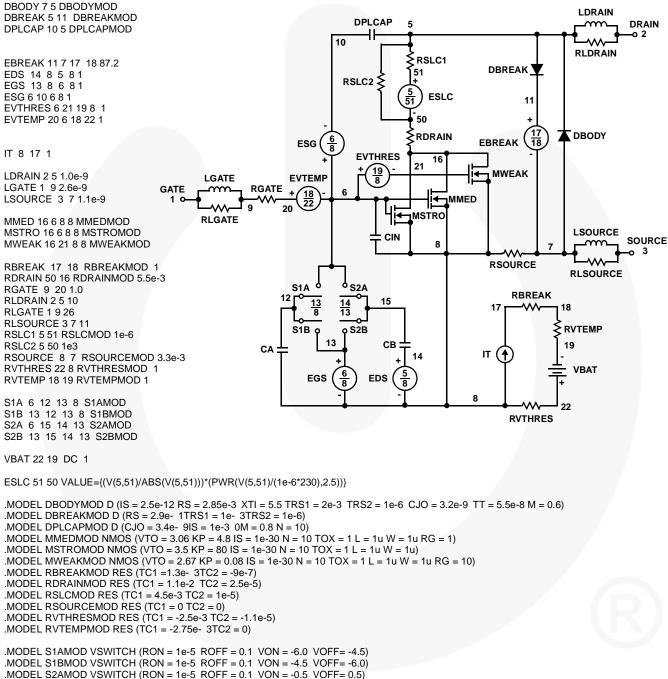


FIGURE 19. SWITCHING TIME WAVEFORM

PSPICE Electrical Model

.SUBCKT HUF75542P3 2 1 3 ; rev 15 Feb 2000

CA 12 8 4.4e-9 CB 15 14 4.2e-9 CIN 6 8 2.5e-9



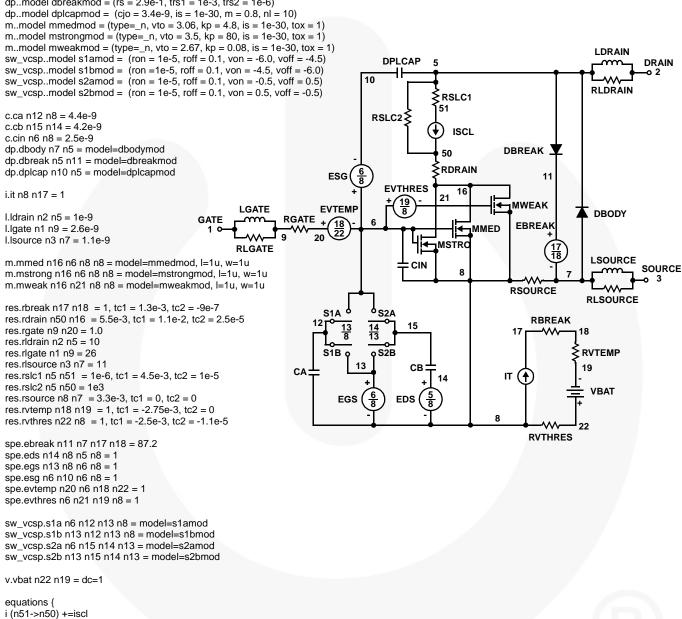
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.5 VOFF = -0.5)

.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

SABER Electrical Model

REV 15 Feb 00 template huf75542p3 n2,n1,n3 electrical n2,n1,n3 { var i iscl dp..model dbodymod = (is = 2.5e-12, rs = 2.85e-3, xti = 5.5, trs1 = 2e-3, trs2 = 1e-6, cjo = 3.2e-9, tt = 5.5e-8, m = 0.6) dp..model dbreakmod = (rs = 2.9e-1, trs1 = 1e-3, trs2 = 1e-6) dp..model dbreakmod = (cjo = 3.4e-9, is = 1e-30, m = 0.8, nl = 10) m..model mmedmod = (type=_n, vto = 3.06, kp = 4.8, is = 1e-30, tox = 1) m..model mstonomod = (type=_n, vto = 3.5, kp = 80, is = 1e-30, tox = 1)



SPICE Thermal Model

REV 15 Feb 00

T75542

CTHERM1 th 6 4.1e-3 CTHERM2 6 5 5.5e-3 CTHERM3 5 4 8.6e-3 CTHERM4 4 3 1.5e-2 CTHERM5 3 2 1.6e-2 CTHERM6 2 tl 6.5e-2

RTHERM1 th 6 2.0e-4 RTHERM2 6 5 3.5e-3 RTHERM3 5 4 2.5e-2 RTHERM4 4 3 9.0e-2 RTHERM5 3 2 1.6e-1 RTHERM6 2 tl 2.3e-1

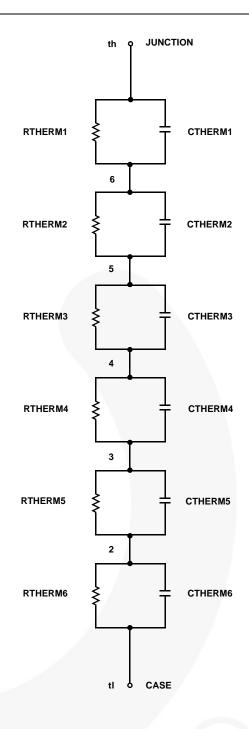
SABER Thermal Model

SABER thermal model t75542

template thermal_model th tl thermal_c th, tl

ctherm.ctherm1 th 6 = 4.1e-3ctherm.ctherm2 6 5 = 5.5e-3ctherm.ctherm3 5 4 = 8.6e-3ctherm.ctherm4 4 3 = 1.5e-2ctherm.ctherm5 3 2 = 1.6e-2ctherm.ctherm6 2 tl = 6.5e-2

rtherm.rtherm1 th 6 = 2.0e-4 rtherm.rtherm2 6 5 = 3.5e-3 rtherm.rtherm3 5 4 = 2.5e-2 rtherm.rtherm4 4 3 = 9.0e-2 rtherm.rtherm5 3 2 = 1.6e-1 rtherm.rtherm6 2 tl = 2.3e-1 }



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